I. <u>IN THE CLAIMS:</u>

- 1. (Canceled)
- 2. (Cancelled)
- 3. (Previously Presented) The method of claim 14, wherein the hydroxylamine derivative is present in a total amount from about 1% to about 20% by weight of the composition.
- 4. (Previously Presented) The method of claim 14, wherein the corrosion inhibitor comprises benzotriazole.
- 5. (Previously Presented) The method of claim 4, wherein the corrosion inhibitor consists essentially of benzotriazole.
- 6. (Previously Presented) The method of claim 5, wherein the corrosion inhibitor is present in a total amount from about 0.01% to about 0.05% by weight of the composition.
- 7. (Previously Presented) The method of claim 14, wherein the water is present in a total amount from about 90% to about 99% by weight of the composition.
- 8. (Previously Presented) The method of claim 14, wherein the composition comprises a sufficient amount of the acid and/or a base to adjust the pH of the composition to a desired level between pH 2 and pH 12.
- 9. (Previously Presented) The method of claim 8, wherein the acid and/or base are present in a total amount from about 0.01% to about 2% by weight of the composition.
- 10. (Currently Amended) The method of claim 14, wherein the composition further comprises one or more of the following: a two carbon atom linkage alkanolamine compound, a

quaternary ammonium salt, a chelating agent, an organic solvent, a non-hydroxyl-containing amine compound, a surfactant, an additional oxidizing agent, and a non-abrasive additive.

- 11. (Canceled)
- 12. (Canceled)
- 13. (Canceled)
- 14. (Currently Amended) A method for chemical mechanical polishing of a substrate comprising:

providing a substantially abrasive-free chemical mechanical polishing composition containing less than 1.0 % by weight abrasive, that comprises a hydroxylamine derivative, a corrosion inhibitor, water, and optionally a sufficient amount of an acid and/or a base to adjust the pH of the composition to a desired level, wherein the majority of the composition comprises water;

contacting the chemical mechanical polishing composition with a substrate having a metal oxide layer surface, upon which metal oxide surface a barrier layer is disposed, upon which barrier layer a metal layer is disposed, and

chemically mechanically polishing the substrate by contacting the substrate surface with an abrasive polishing pad at an applied pressure of not more than about 2 psi and by moving the pad in relation to the substrate,

wherein:

the removal rate of the barrier layer is greater than about 500 Å/min, wherein the removal rate of the metal oxide layer is less than about 10 Å/min, wherein the removal rate of the metal layer is less than about 250 Å/min, [[and]] wherein the hydroxylamine derivative is substantially free of hydroxylamine, and the composition further comprises a two-carbon atom linkage alkanolamine compound.

15. (Cancelled)

- 16. (Previously Presented) The method of claim 14, wherein the removal rate of the metal layer during the chemical mechanical polishing step is greater than about 10 Å/min.
- 17. (Previously Presented) The method of claim 14, wherein the removal rate of the barrier layer during the chemical mechanical polishing step is less than about 750 Å/min.
- 18. (Currently Amended) The method of claim 14, wherein the abrasive-free chemical mechanical polishing composition is substantially free of one or more of the following: acid and/or base to adjust pH, two carbon atom linkage alkanolamine compounds, quaternary ammonium salts, chelating agents, organic solvents, non-hydroxyl-containing amine compounds, surfactants, additional oxidizing agents, and non-abrasive additives.
- 19. (Currently Amended) The method of claim 14, wherein the abrasive-free chemical mechanical polishing composition consists essentially of:

about 1% to about 5% by weight of a hydroxylamine derivative selected from the group consisting of hydroxylamine nitrate, hydroxylamine sulfate, and mixtures thereof;

about 0.01% to about 0.05% by weight of benzotriazole;

about 90% to 99% by weight of water; and

less than about 2% by weight of the acid and/or a base to adjust the pH of the composition to a desired level-, and

a two carbon atom linkage alkanolamine compound.

20. (Canceled)

- 21. (Previously Presented) The method of claim 14, wherein the metal layer of the substrate comprises copper.
- 22. (Previously Presented) The method of claim 21, wherein the barrier layer of the substrate comprises tantalum nitride.

- 23. (Previously Presented) The method of claim 14, wherein the barrier layer of the substrate comprises tantalum nitride.
- 24. (Currently Amended) The method of claim 14, wherein the pH of the composition is about between about 4 and about 10.
- 25. (Currently Amended) The method of claim 14, wherein the pH of the composition is about between about 5.2 and about 5.5.
- 26. (Previously Presented) The method of claim 14, wherein the hydroxylamine derivative is present in a total amount from about 0.2% to about 20% by weight of the composition and wherein the concentration of the acid and/or a base to adjust the pH of the composition is from about 0.01 to about 1%.
- 27. (Currently Amended) A method for chemical mechanical polishing of a substrate comprising:

providing a substantially abrasive-free chemical mechanical polishing composition containing less than 1.0 % by weight abrasive, that comprises a hydroxylamine derivative, a corrosion inhibitor, water, and optionally a sufficient amount of an acid and/or a base to adjust the pH of the composition to a desired level, wherein the majority of the composition comprises water;

contacting the chemical mechanical polishing composition with a substrate having a metal oxide layer surface, upon which metal oxide surface a barrier layer is disposed, upon which barrier layer a metal layer is disposed, and

chemically mechanically polishing the substrate by contacting the substrate surface with an abrasive polishing pad at an applied pressure of not more than about 2 psi and by moving the pad in relation to the substrate,

wherein:

the removal rate of the barrier layer is between 200 and 580 Å/min, and wherein the removal rate of the metal oxide layer is less than about 10 Å/min, wherein the removal rate of the metal layer is less than about 250 Å/min; and

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wherein the hydroxylamine derivative is substantially free of hydroxylamine-; and the composition further comprises a two-carbon atom linkage alkanolamine compound.

- 28. (Previously Presented) The method of claim 14 wherein the hydroxylamine derivative comprises hydroxylamine nitrate.
- 29. (Previously Presented) The method of claim 14 wherein the hydroxylamine derivative comprises hydroxylamine sulfate.
- 30. (Currently Amended) [[A]] <u>The</u> method of claim 14 wherein the hydroxylamine derivative comprises hydroxylamine sulfate and hydroxylamine nitrate.
- 31. (Previously Presented) The method of claim 27 wherein the hydroxylamine derivative comprises hydroxylamine nitrate.
- 32. (Previously Presented) The method of claim 27 wherein the hydroxylamine derivative comprises hydroxylamine sulfate.
- 33. (Currently Amended) [[A]] <u>The</u> method of claim 27 wherein the hydroxylamine derivative comprises hydroxylamine sulfate and hydroxylamine nitrate.